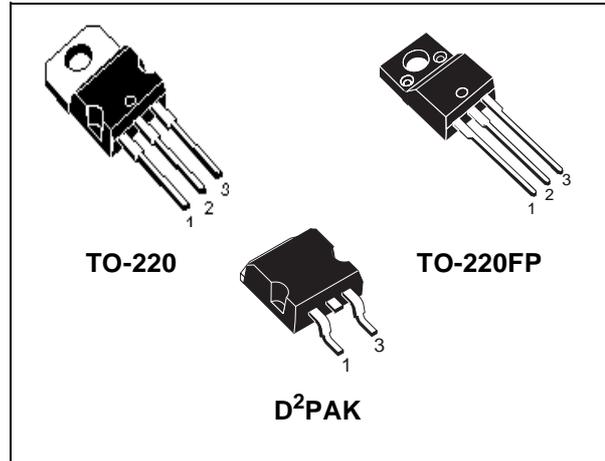


## N-CHANNEL 500V - 0.48Ω - 10A TO-220/TO-220FP/D<sup>2</sup>PAK Zener-Protected SuperMESH™ Power MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>	P <sub>w</sub>
STB11NK50Z	500 V	< 0.52 Ω	10 A	125 W
STP11NK50Z	500 V	< 0.52 Ω	10 A	125 W
STP11NK50ZFP	500 V	< 0.52 Ω	10 A	30 W

- TYPICAL R<sub>DS(on)</sub> = 0.48 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATABILITY
- ADD SUFFIX "T4" FOR ORDERING IN TAPE & REEL (D<sup>2</sup>PAK VERSION)



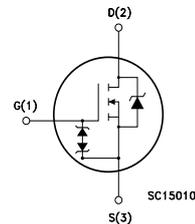
### DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- IDEAL FOR OFF-LINE POWER SUPPLIES, ADAPTORS AND PFC
- LIGHTING

### INTERNAL SCHEMATIC DIAGRAM



### ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STB11NK50ZT4	B11NK50Z	D <sup>2</sup> PAK	TAPE & REEL
STP11NK50Z	P11NK50Z	TO-220	TUBE
STP11NK50ZFP	P11NK50ZFP	TO-220FP	TUBE

## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		TO-220 / D <sup>2</sup> PAK	TO-220FP	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	500		V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	500		V
V <sub>GS</sub>	Gate- source Voltage	± 30		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	10	10(*)	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	6.3	6.3(*)	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	40	40(*)	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	125	30	W
	Derating Factor	1	0.24	W/°C
V <sub>ESD(G-S)</sub>	Gate source ESD(HBM-C=100pF, R=1.5KΩ)	4000		V
dv/dt (1)	Peak Diode Recovery voltage slope	4.5		V/ns
Viso	Insulation Withstand Voltage (DC)	--	2500	V
T <sub>j</sub>	Operating Junction Temperature	-55 to 150		°C
T <sub>stg</sub>	Storage Temperature	-55 to 150		°C

(•) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 10A, di/dt ≤ 200A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

(\*) Limited only by maximum temperature allowed

## THERMAL DATA

		TO-220 / D <sup>2</sup> PAK	TO-220FP	
R <sub>thj-case</sub>	Thermal Resistance Junction-case Max	1	4.2	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient Max	62.5		°C/W
T <sub>I</sub>	Maximum Lead Temperature For Soldering Purpose	300		°C

## AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max)	10	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	190	mJ

## GATE-SOURCE ZENER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV <sub>GSO</sub>	Gate-Source Breakdown Voltage	I <sub>gs</sub> = ± 1mA (Open Drain)	30			V

**ELECTRICAL CHARACTERISTICS (TCASE =25°C UNLESS OTHERWISE SPECIFIED)  
ON/OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 1mA, V_{GS} = 0$	500			V
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}, T_C = 125^\circ\text{C}$			1 50	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body Leakage Current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20V$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 100\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V, I_D = 5\text{ A}$		0.48	0.52	$\Omega$

**DYNAMIC**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (1)$	Forward Transconductance	$V_{DS} = 15V, I_D = 5\text{ A}$		7.7		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25V, f = 1\text{ MHz}, V_{GS} = 0$		1390 173 42		pF pF pF
$C_{oss\text{ eq.}} (3)$	Equivalent Output Capacitance	$V_{GS} = 0V, V_{DS} = 0V\text{ to }400V$		110		pF

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{DD} = 250\text{ V}, I_D = 5.5\text{ A}$ $R_G = 4.7\Omega, V_{GS} = 10\text{ V}$ (Resistive Load see, Figure 3)		14.5 18		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 400V, I_D = 11.4\text{ A},$ $V_{GS} = 10V$		49 10 25	68	nC nC nC

**SWITCHING OFF**

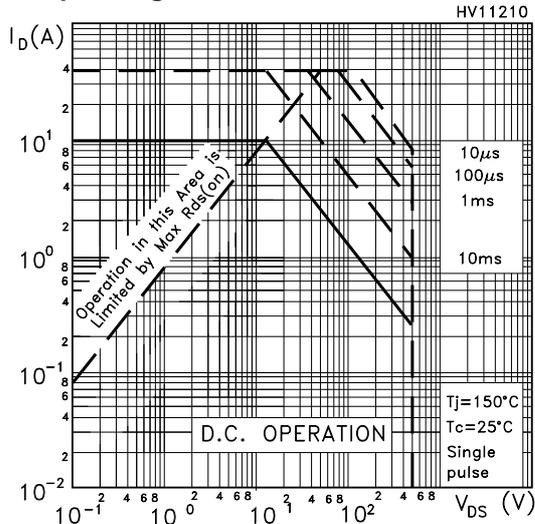
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ $t_f$	Turn-off Delay Time Fall Time	$V_{DD} = 250\text{ V}, I_D = 5.5\text{ A}$ $R_G = 4.7\Omega, V_{GS} = 10\text{ V}$ (Resistive Load see, Figure 3)		41 15		ns ns
$t_r(V_{off})$ $t_f$ $t_c$	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 400V, I_D = 11.4\text{ A},$ $R_G = 4.7\Omega, V_{GS} = 10V$ (Inductive Load see, Figure 5)		11.5 12 27		ns ns ns

**SOURCE DRAIN DIODE**

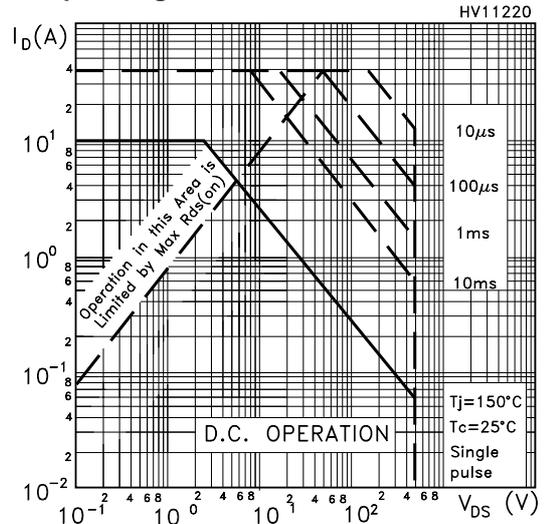
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM} (2)$	Source-drain Current Source-drain Current (pulsed)				10 40	A A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 10\text{ A}, V_{GS} = 0$			1.6	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 10\text{ A}, di/dt = 100A/\mu\text{s}$ $V_{DD} = 36V, T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		308 2.4 16		ns nC A

- Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.  
3.  $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

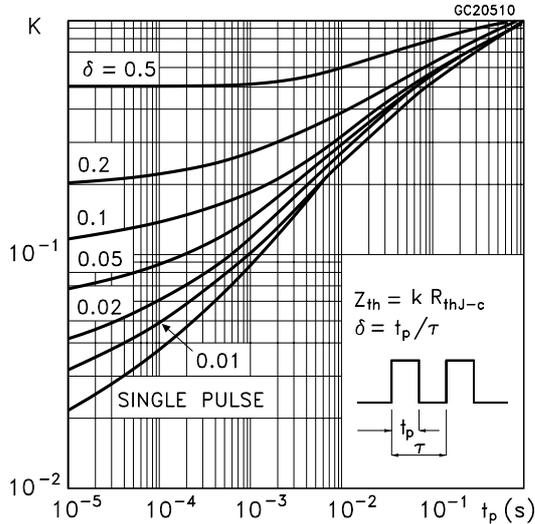
### Safe Operating Area For TO-220 / D2PAK



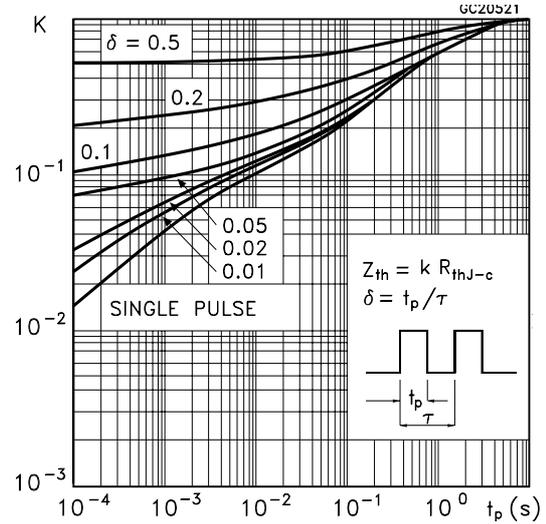
### Safe Operating Area For TO-220FP



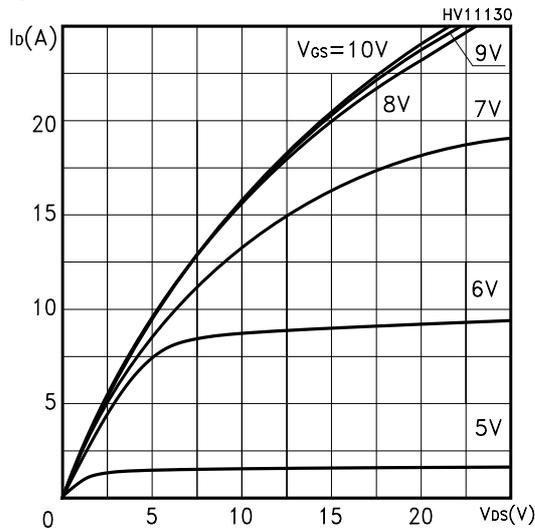
### Thermal Impedance For TO-220 / D2PAK



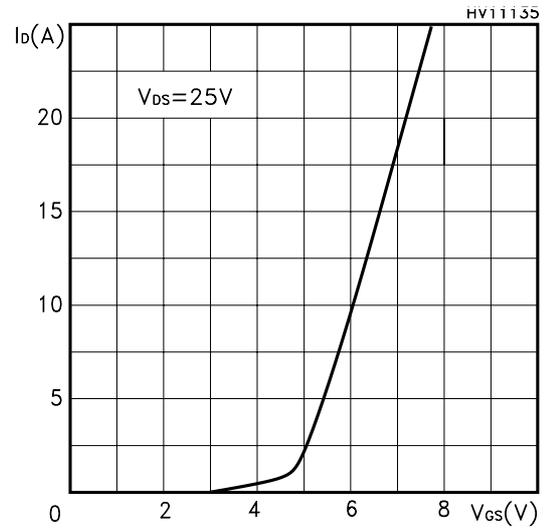
### Thermal Impedance For TO-220FP



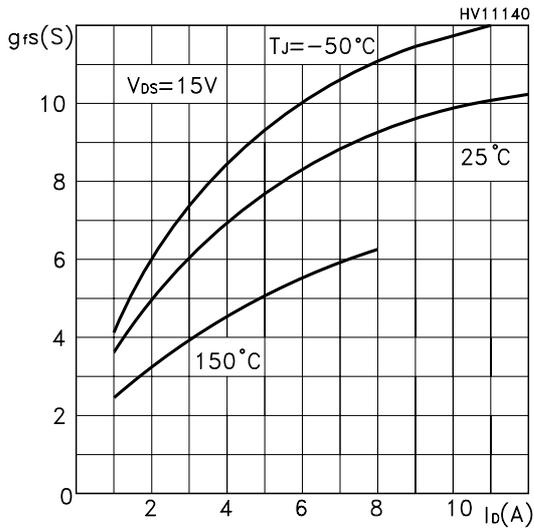
### Output Characteristics



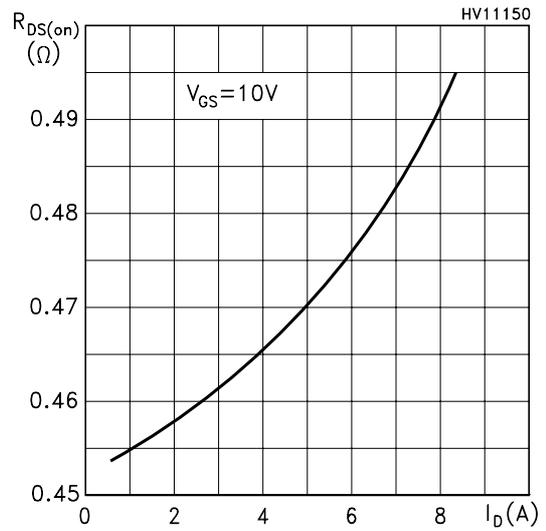
### Transfer Characteristics



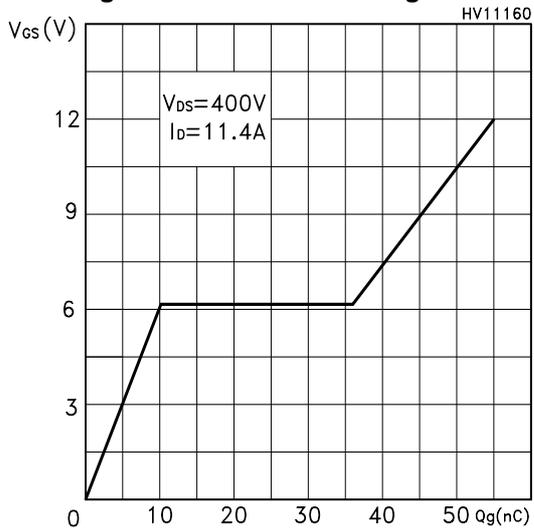
**Transconductance**



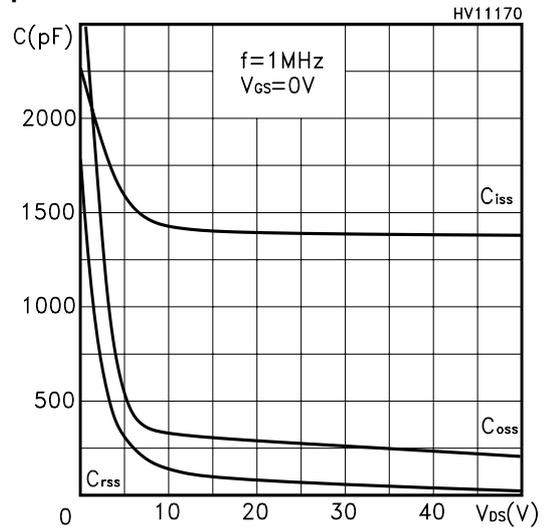
**Static Drain-source On Resistance**



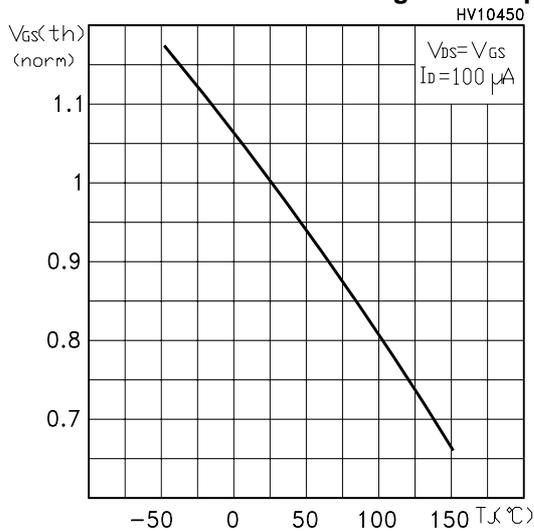
**Gate Charge vs Gate-source Voltage**



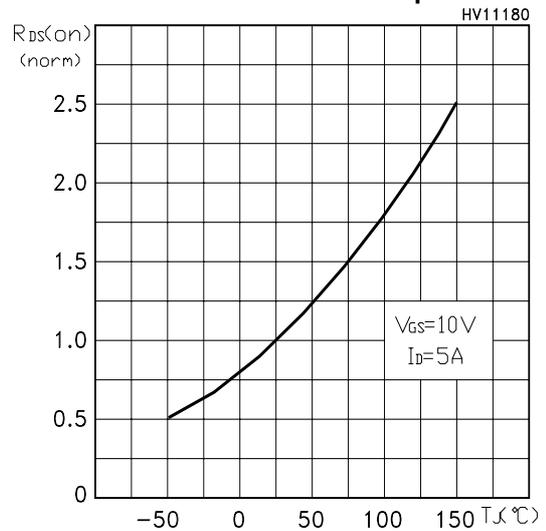
**Capacitance Variations**



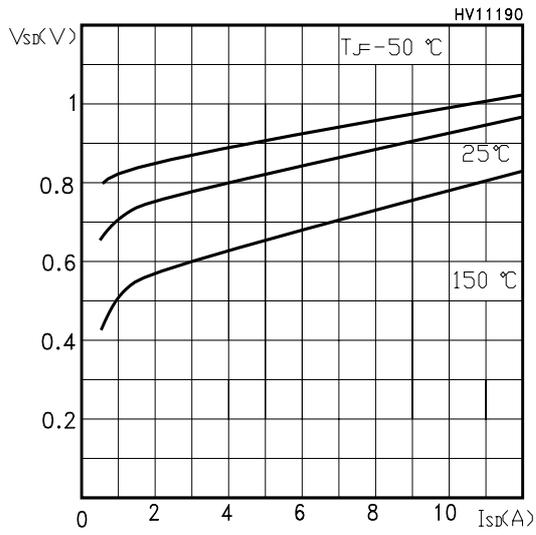
**Normalized Gate Threshold Voltage vs Temp.**



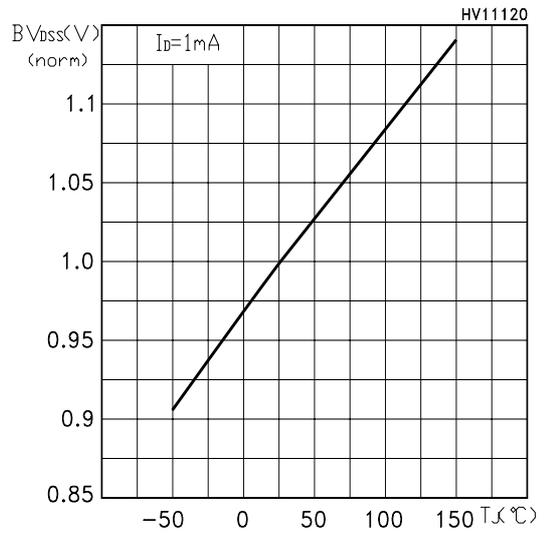
**Normalized On Resistance vs Temperature**



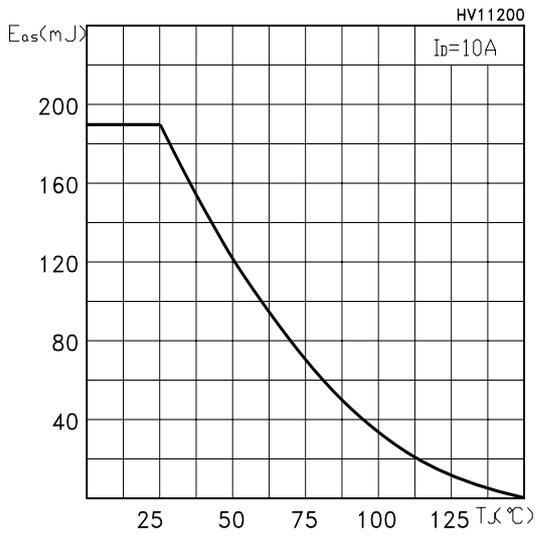
**Source-drain Diode Forward Characteristics**



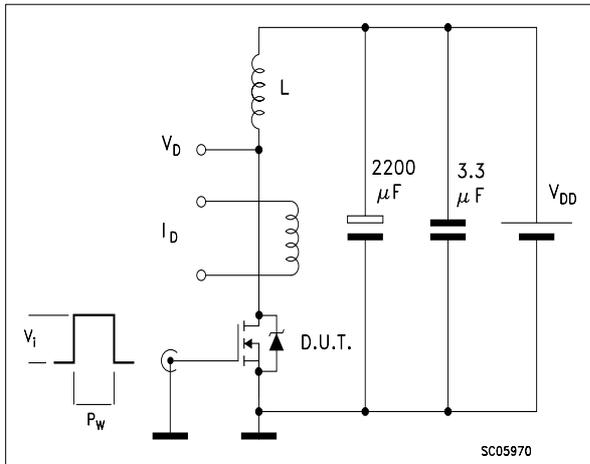
**Normalized BVDSS vs Temperature**



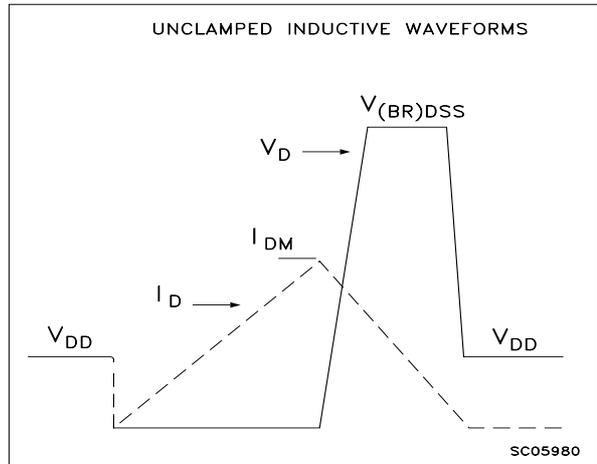
**Maximum Avalanche Energy vs Temperature**



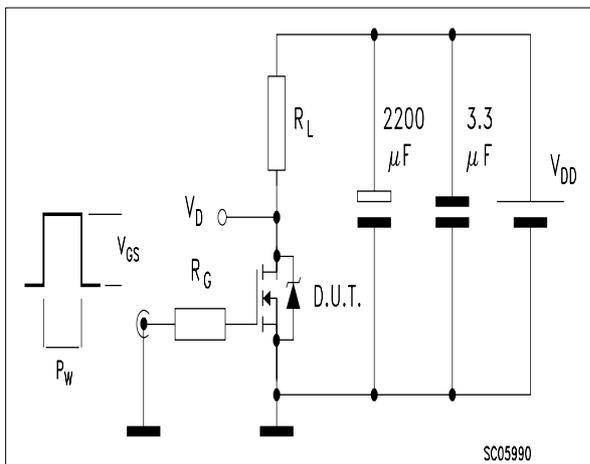
**Fig. 1: Unclamped Inductive Load Test Circuit**



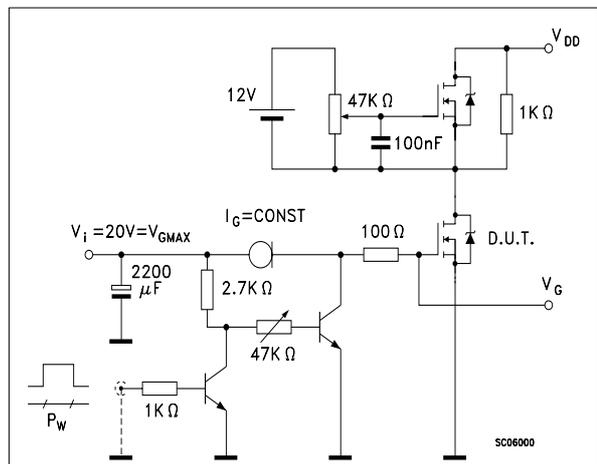
**Fig. 2: Unclamped Inductive Waveform**



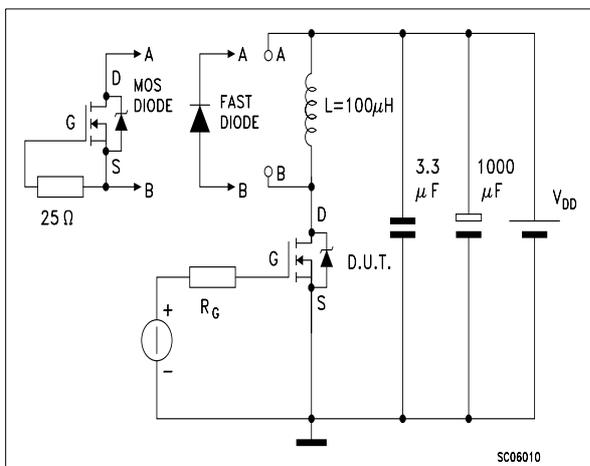
**Fig. 3: Switching Times Test Circuit For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

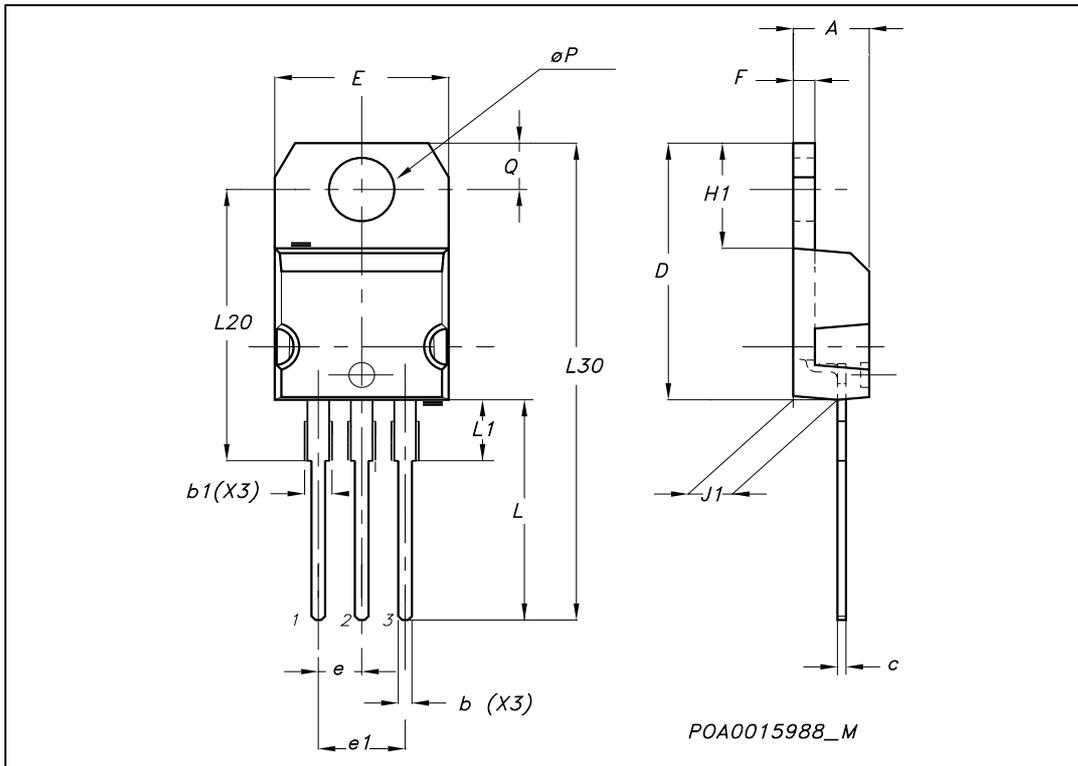


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



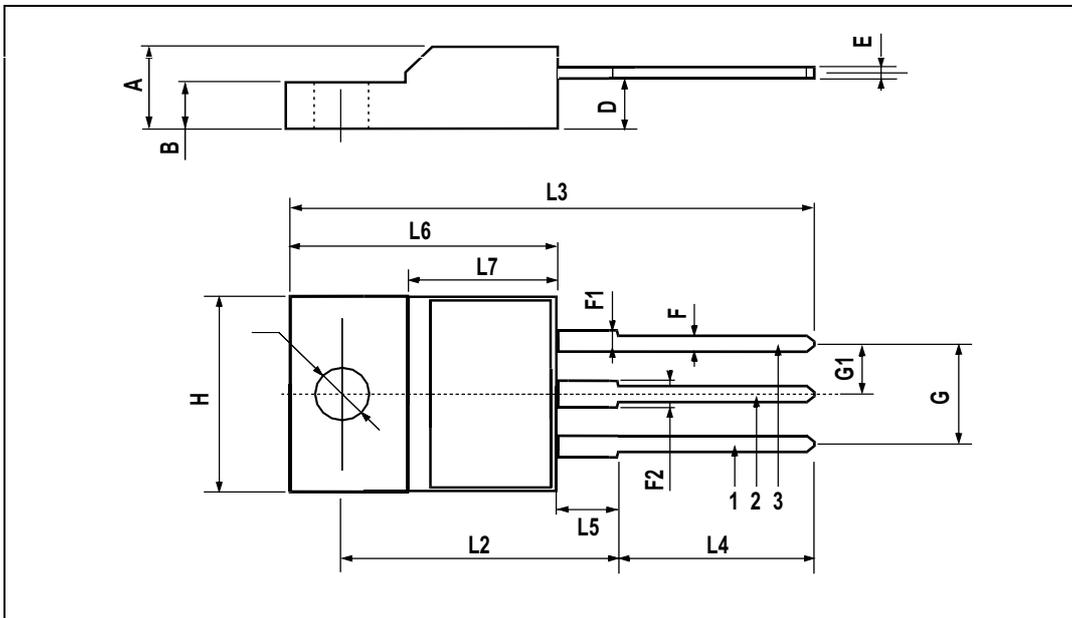
## TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



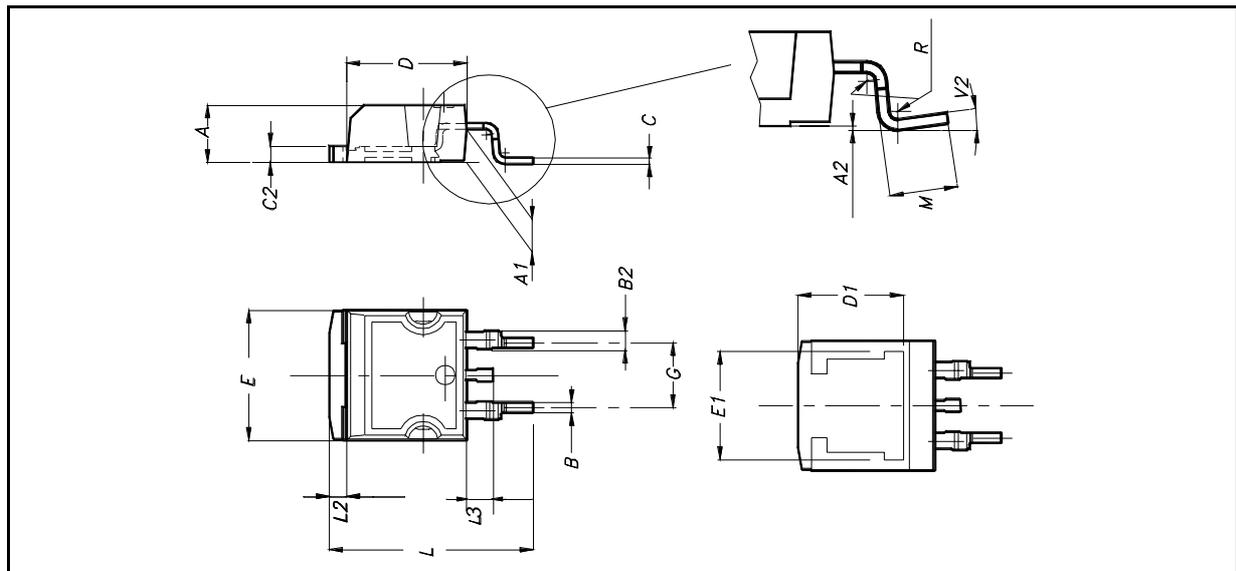
## TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
∅	3		3.2	0.118		0.126

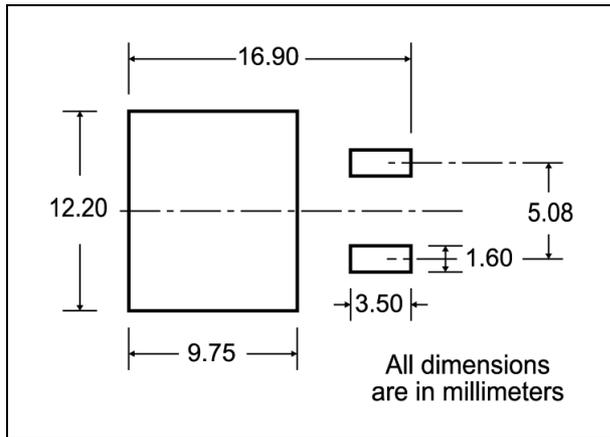


## D<sup>2</sup>PAK MECHANICAL DATA

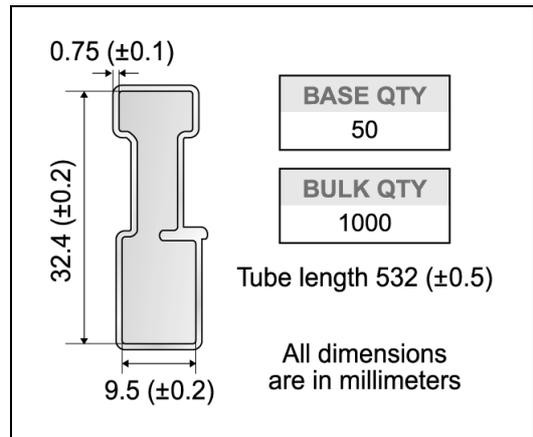
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



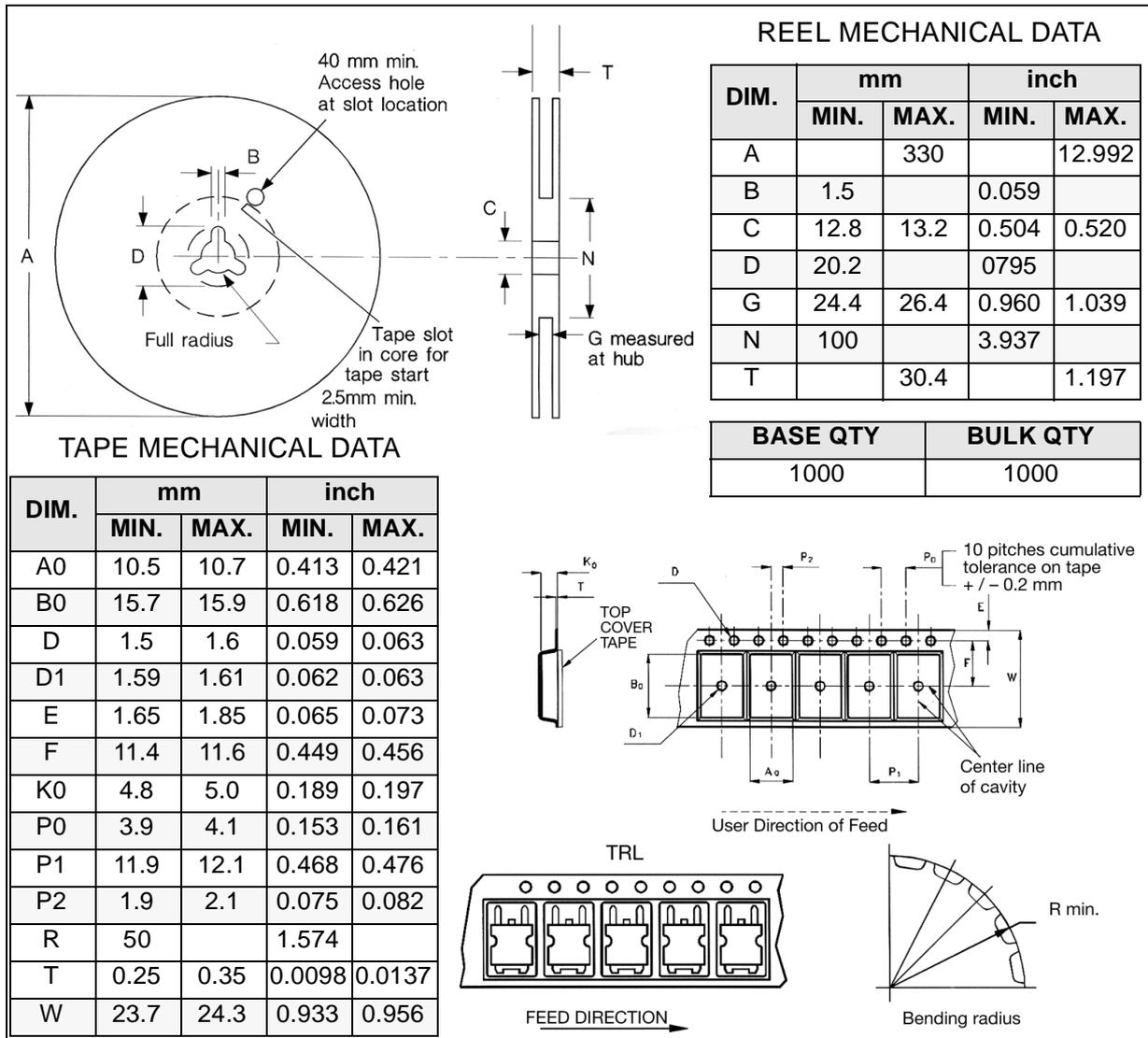
## D<sup>2</sup>PAK FOOTPRINT



## TUBE SHIPMENT (no suffix)\*



## TAPE AND REEL SHIPMENT (suffix "T4")\*



\* on sales type